L Number	Hits	Search Text	DB	Time stamp
2	5270	(430/311-313).CCLS.	USPAT;	2004/06/24
	02.0	(400/011-010/.00201	US-PGPUB;	14:18
4		·	1	14:10
			EPO; JPO;	-
		· ·	DERWENT;	
	40	//400/044 040) 0010 > 1//000 = 5550	IBM_TDB	
	19	((430/311-313).CCLS.) and ((ARC or BARC or	USPAT;	2004/06/24
		anti\$2reflect\$5) same ((Si\$3N or (silicon	US-PGPUB;	14:30
		near nitride)) with poly\$silicon))	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
7	3211	(438/257,260,424,786).CCLS.	USPAT;	2004/06/24
			US-PGPUB;	14:44
			EPO; JPO;	
			DERWENT;	*
			IBM_TDB	
8	486	((438/257,260,424,786).CCLS.) and (STI or	USPAT;	2004/06/24
		(trench near isolation)) and (ARC o rBARC	US-PGPUB;	14:44
		or anti\$2reflect\$5)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	-
10	127	(((438/257,260,424,786).CCLS.) and (STI or	USPAT;	2004/06/24
	121	•	1	2004/06/24
		(trench near isolation)) and (ARC o rBARC	US-PGPUB;	15:02
		or anti\$2reflect\$5)) and (\$TI or (trench near	EPO; JPO;	- 4-
		isolation)) and (ARC or BARC or	DERWENT;	
11		anti\$2reflect\$5)	IBM_TDB	
	584	(427/255.28).CCLS.	USPAT;	2004/06/24
			US-PGPUB;	15:03
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
12	2	((427/255.28).CCLS.) and ((ARC or BARC or	USPAT;	2004/06/24
		anti\$2reflect\$5) same ((Si\$3N or (silicon	US-PGPUB;	15:04
		near nitride)) with poly\$silicon))	EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	
13	306	(resist or photo\$resist) and (Azuma.in. or	USPAT;	2004/06/24
		flaim.in.)	US-PGPUB;	15:05
		-	EPO; JPO;	10.00
			DERWENT;	
	÷		IBM_TDB	
	17681	(trench near isolation)	_	2004/06/47
	1,001	(II ear Isviation)	USPAT;	2004/06/17
			US-PGPUB;	21:46
			EPO; JPO;	
			DERWENT;	
į			IBM_TDB	
-	2973	(trench near isolation) and (pad near oxide)	USPAT;	2004/06/17
			US-PGPUB;	21:46
			EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	

*				
	1870	(trench near isolation) and (pad near oxide)	USPAT;	2004/06/17
		and (poly or poly\$1silicon)	US-PGPUB;	21:46
		· ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	36	(trench near isolation) and (pad near oxide)	USPAT;	2004/06/24
		and (poly or poly\$1silicon) and	US-PGPUB;	11:44
		(Anti\$4refelect\$7 or BARC)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	390	(trench near isolation) and (filler same	USPAT;	2004/06/17
		material)	US-PGPUB;	21:51
	-		EPO; JPO;	
			DERWENT:	* •
			IBM_TDB	
•	396	(trench near isolation) and (filler same	USPAT;	2004/06/17
		(oxide or dielectric))	US-PGPUB;	21:51
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
-	315	(trench near isolation) and (filler with	USPAT;	2004/06/17
		(oxide or dielectric))	US-PGPUB;	21:51
			EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
•	230	(trench near isolation) and (filler near4	USPAT;	2004/06/17
	1	(oxide or dielectric))	US-PGPUB;	21:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	146	(trench near isolation) and (filler near	USPAT;	2004/06/17
		(oxide or dielectric))	US-PGPUB;	21:52
		*	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	(trench near isolation) and (pad near oxide)	USPAT;	2004/06/17
		and (poly or poly\$1silicon) and	US-PGPUB;	21:53
		(Anti\$4refelect\$7 or BARC) and (filler or	EPO; JPO;	
		dielectric)	DERWENT;	
			IBM_TDB	
	44	"5886391" or "5930644" or "576262" or	USPAT;	2004/06/23
		EP0908938 or EP0819786	US-PGPUB;	17:31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	